

Supplementary Information

Durable polymer solar cells produced by encapsulation of WSe₂ hole-transport layer and β -Carotene as active layer additive

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EXPERIMENTAL SECTION

1 Methods

1.1 Liquid-phase exfoliation of WSe₂

100 mg of bulk WSe₂ powders (5 μ m, purity >98 %, Sigma-Aldrich) were dispersed in the NaOH/urea (molar ratio = 1 : 2) dispersion. After that, 200 mL of the WSe₂ dispersion were moved to a 500 mL glass beaker, where WSe₂ powders were exfoliated and dispersed via pure mechanical stirring at speed of 1200 rpm for 24 h. Besides, the acquired products were divided equally to 50 ml centrifugal tubes, then maintained at 3000 rpm for 15 min. Take advantage of the top half of the dispersion and re-mixed in DMF, subsequently clearing in ultrasonic baths and filtration with abundant DMF, deionized water and ethanol. Finally removed excess solvents in vacuum oven at 50 °C. The yield of WSe₂ nanoflakes (NF-WSe₂) was figured by eliminating the mass of the residual solid.

1.2 PSCs fabrication

Glass/ITO substrates (resistance = 20 Ω /sq) were thoroughly washed by ultrasonic machine in deionized water, anhydrous ethanol, acetone, and isopropyl alcohol, respectively. After that, the ablent substrates were uncovered in ultraviolet-ozone chamber for 20 min. In view of the structure and fabrication of PSCs, the 0.5 mg mL⁻¹ dispersion (IPA) of NF-WSe₂ was spin coated at 1000 rpm for 30 s for limited times to fulfil the stated thickness without other treatment. Besides, PEDOT:PSS (Clevios 4083) was spin coated onto Glass/ITO at 6000 rpm for 60 s and annealed at 150 °C for 5 min in air to form a 40 nm thick film. The processed substrates were all moved into a glovebox. 100 nm thick PCDTBT: PC₇₁BM+bCar active layer was achieved by casting 15 mg mL⁻¹ solution (PCDTBT: PC₇₁BM = 1:4 by wt., dissolved in 1, 2-dichlorobenzene with 3 wt. % bCar) at 1400 rpm. Additionally, 90 nm thick PBDB-T: PC₇₁BM+bCar active layer was also achieved by casting 20 mg mL⁻¹ solution (PCDTBT: PC₇₁BM = 2: 3 by wt., dissolved in 1, 2-dichlorobenzene with 3 wt. % bCar) at 1100 rpm, and treated by thermal annealing at 150 °C for 10 min. Then, the devices were stored in a glovebox-embedded thermal evaporator and pumped under a background pressure of 2×10^{-6} Torr. At last, a layer of 10 nm Ca and 100 nm thick Ag were thermally deposited as the top electrode through shadow masks by thermal evaporation.

2 Measurements and characterization

The crystallographic planes of related samples were characterized using powder X-Ray diffraction (PXRD) with Cu Ka radiation ($\lambda = 1.54060$ Å). The high-resolution transmission electron microscopy (HRTEM) images were taken on JEM-2100F at 200 kV accelerating voltage. Elemental mapping and EDS were performed with JSM-5160LV-Vantage typed energy spectrometer. The morphology image was obtained by

a SEM (Hitachi SU8010). X-ray photoelectron spectroscopy (XPS) spectra were obtained with a Ulvac-PHI5000 Versaprobe III spectrometer using a Al k source (1486.6 eV). Film thickness was measured using a spectroscopic ellipsometer (J. A. Woollam, USA). The electronic properties of all films were characterized by ultraviolet photoelectron spectroscopy (UPS) using the He I (21.22 eV) excitation line. The Raman spectra were collected using a HORIBA XploRA plus system with a 633 nm laser. Thermogravimetric analysis and differential scanning calorimetry (TG-DSC) was collected using a TA SDT-Q600 with a heating rate of 10 °C/min from 25 to 800 °C in air flow. The UV-absorption spectra of the WSe₂ dispersion were recorded on a spectrophotometer (Shimadzu UV-2550). AFM images were taken on a Bruker Dimension® Icon Scanning Probe Microscope.

The current density-voltage ($J-V$) curves of the devices were measured with Keithley 2450 source meter unit under 1 sun, the simulated AM 1.5G illumination from a xenon solar simulator (Newport) in air. The light intensity was calibrated with a standard newport standard silicon photovoltaic reference cell. The external quantum efficiency (EQE) measurements were obtained from a QE-3011 system with Newport standard Si diode. Impedance spectra were performed with a PARSTAT 4000A potentiostat and coupled with the Modulab ECS software. The Impedance spectroscopy (IS) data were recorded in the frequency of 1 Hz to 100 kHz by a 10 mV perturbation under dark.

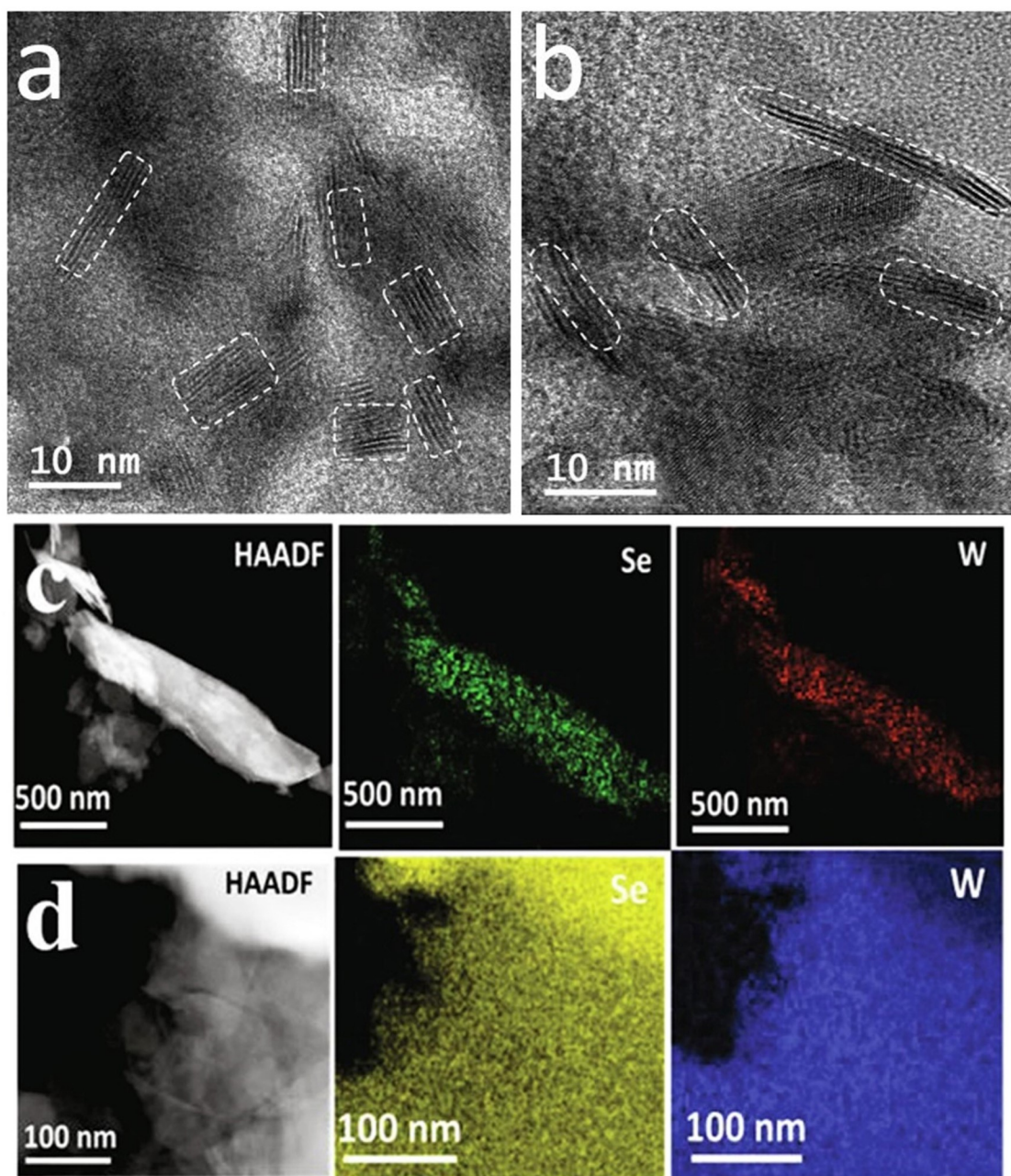


Fig. s1. TEM images of obtained NF-WSe₂ nanocrystals (a, b). The HAADF images of obtained NF-WSe₂ and elemental mapping of Se and W, obtained via EDS (c, d).

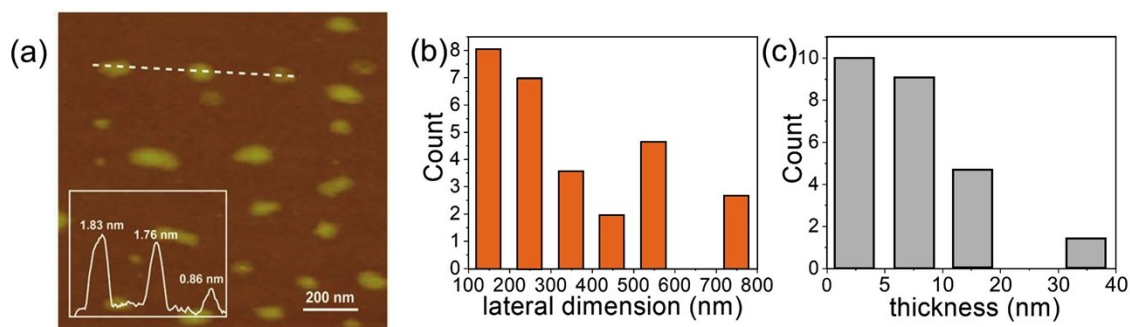


Fig. s2. AFM image of obtained NF-WSe₂ nanocrystals (a). Insets: cross section height profiles. Lateral dimension (b) and thickness (c) distributions of NF-WSe₂ flakes extracted from (a).

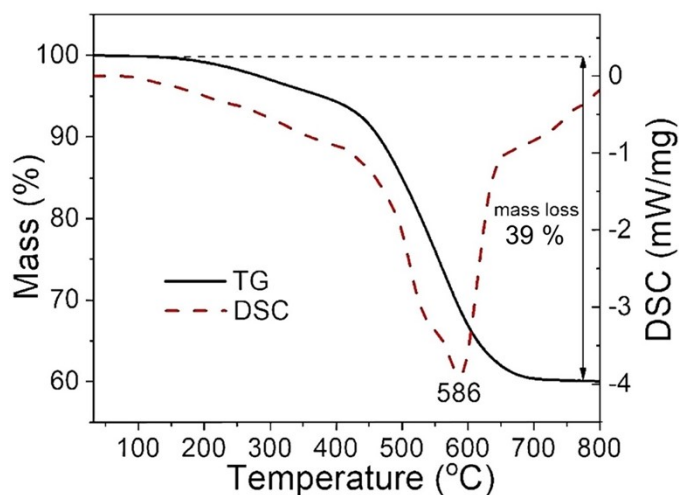


Fig. s3. TG-DSC curves of NF-WSe₂ in an air atmosphere. The thermal stability of NF-WSe₂ in air was confirmed by TG-DSC analysis from room temperature to 800 °C under air. As displayed in Fig. S3, the conversion of WSe₂ revised the maximum exothermic peak at about 586 °C and the final mass loss of 39 %. The decline is caused by the oxidation of NF-WSe₂ to solid WO₃ and gaseous SeO₂.

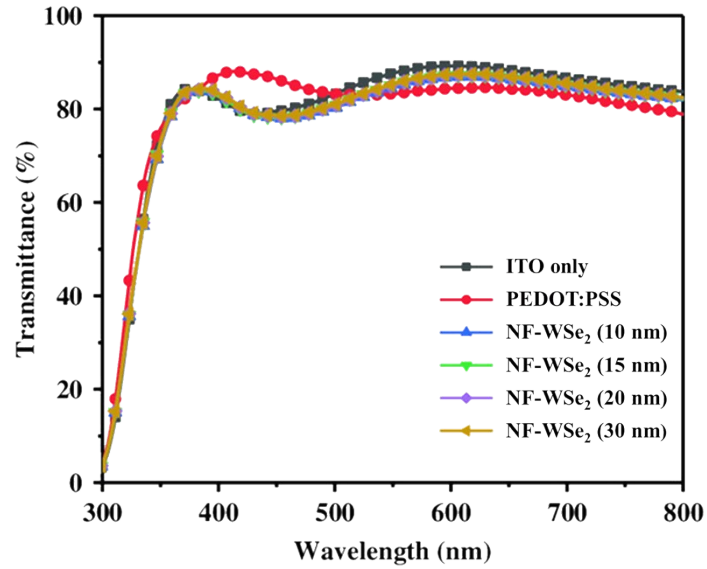


Fig. s4. Transmittance spectra of ITO/glass, PEDOT:PSS/ITO/glass and NF-WSe₂/ITO/glass at various spin-coated thicknesses.

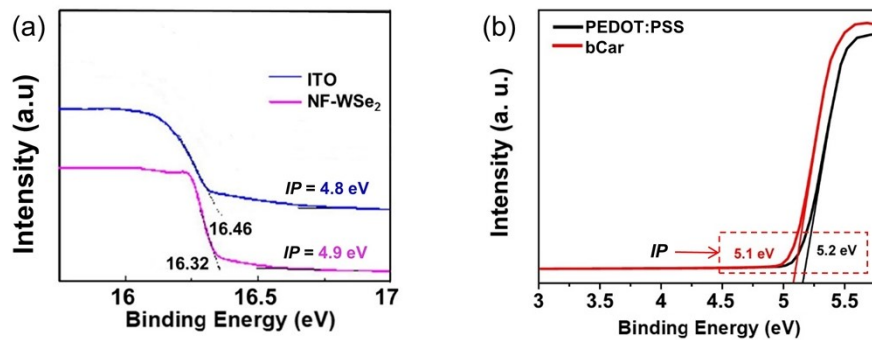


Fig. s5. (a) UPS spectra of the secondary electron cut-off regions of bare ITO and NF-WSe₂ and the corresponding Ionization potentials (*IP*). (b) *IP* curves of PEDOT:PSS and bCar transformed from UPS measurement.

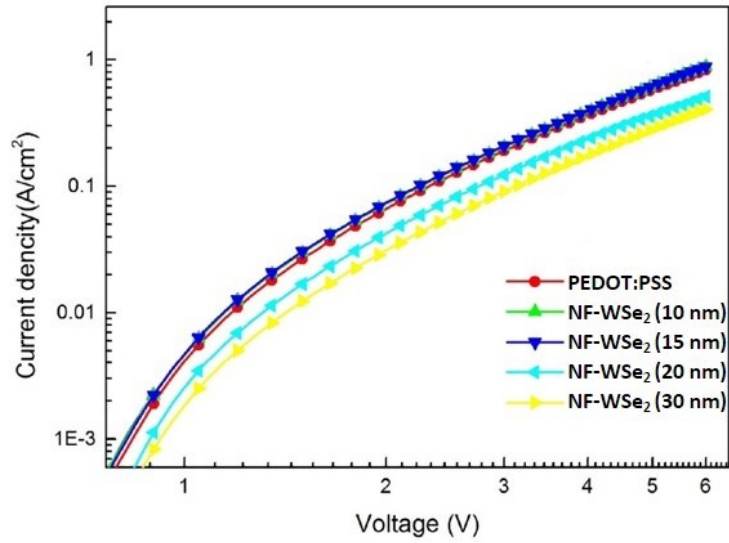


Fig. s6. J - V curves of hole-only devices with the configuration of ITO/NF-WSe₂ or PEDOT:PSS/PCDTBT:PC₇₁BM+bCar/MoO₃/Ag.

Table s1. Hole mobility of the hole-only devices calculated by the SCLC method.

Devices	Hole mobility μ_h (cm ² V ⁻¹ s ⁻¹)
ITO/PEDOT:PSS/PCDTBT:PC ₇₁ BM+bCar/MoO ₃ /Ag	1.33×10^{-4}
ITO/NF-WSe ₂ (10 nm)/PCDTBT:PC ₇₁ BM+bCar/MoO ₃ /Ag	1.25×10^{-4}
ITO/NF-WSe ₂ (15 nm)/PCDTBT:PC ₇₁ BM+bCar/MoO ₃ /Ag	1.21×10^{-4}
ITO/NF-WSe ₂ (20 nm)/PCDTBT:PC ₇₁ BM+bCar/MoO ₃ /Ag	7.68×10^{-5}
ITO/NF-WSe ₂ (30 nm)/PCDTBT:PC ₇₁ BM+bCar/MoO ₃ /Ag	6.52×10^{-5}

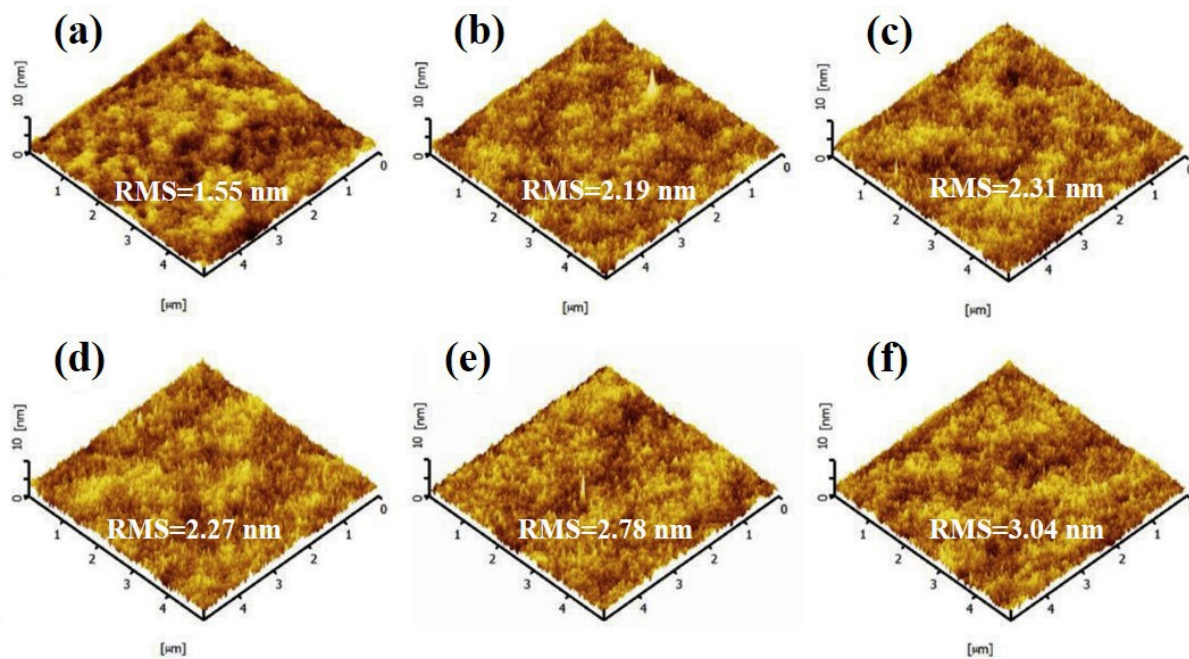


Fig. s7. AFM images as tapping-mode topography of ITO(a) , ITO/PEDOT:PSS(b), ITO/NF-WSe₂(10 nm) (c), (15 nm) (d), (20 nm) (e), (30 nm) (f).

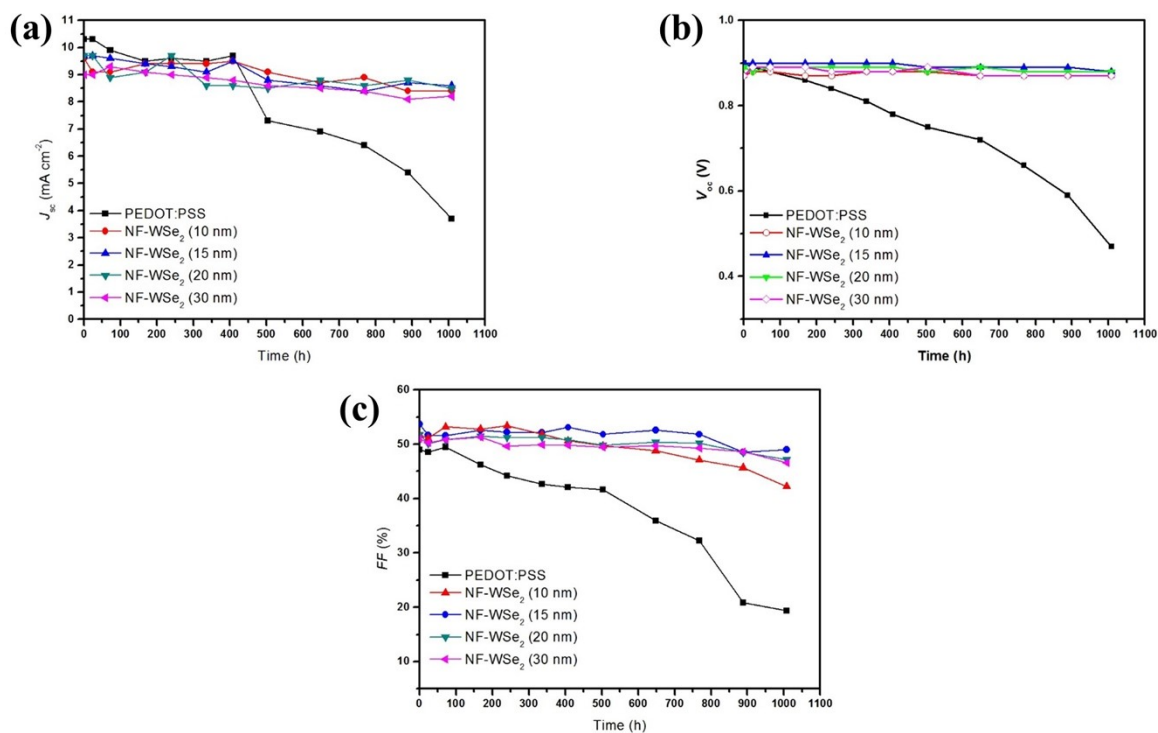


Fig. s8. Long term stability analysis of key photovoltaic parameters (J_{sc} , V_{oc} , and FF) of PSCs with PEDOT:PSS and NF-WSe₂ at various spin-coated thicknesses.

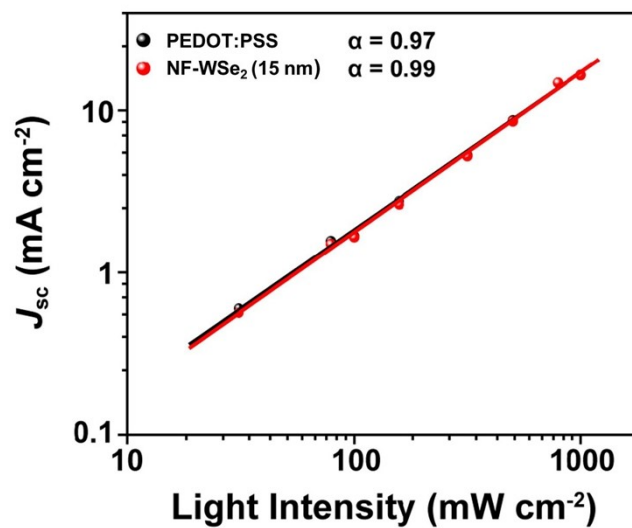


Fig. s9. J_{sc} as a function of light intensity for devices with PEDOT:PSS and NF-WSe₂ (15 nm)

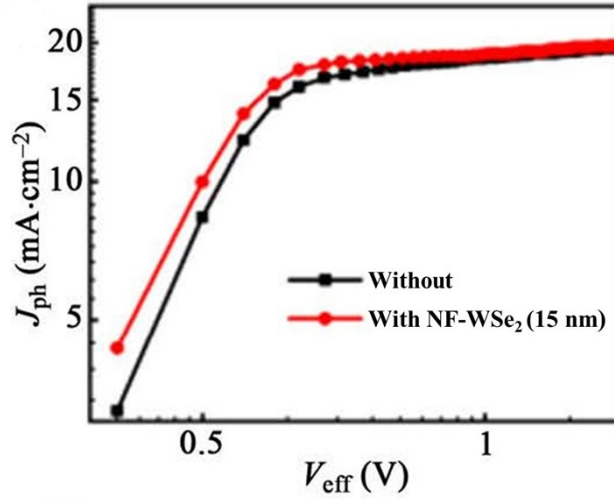


Fig. s10. J_{ph} versus V_{eff} curves of NF-WSe₂ devices.

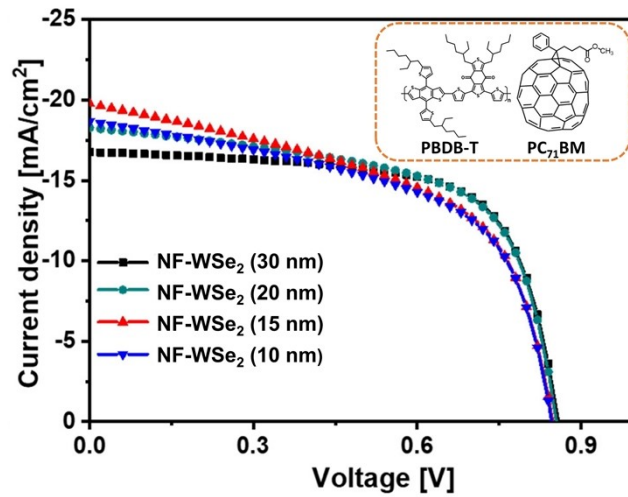


Fig. s11. J - V characteristics of PSCs made by PBDB-T:PC₇₁BM+bCar active layers with NF-WSe₂ for HTL at various spin-coated thicknesses.

Table s2. Summary of photovoltaic operating parameters for PBDB-T:PC₇₁BM+bCar PSCs made with different HTLs, measured under illumination of AM 1.5G (100 mW cm⁻²).

Active layer	HTL	J_{sc} (mA cm ⁻²)	V_{oc} (V)	FF (%)	PCE_{max} (PCE_{avg}) (%)
PBDB-T:PC ₇₁ BM+bCar	NF-WSe ₂ (10 nm)	16.8	0.84	56	8.2 (8.1±0.09)
	NF-WSe ₂ (15 nm)	18.1	0.85	54	8.5 (8.3±0.17)
	NF-WSe ₂ (20 nm)	19.6	0.85	55	9.2 (9.1±0.14)
	NF-WSe ₂ (30 nm)	18.6	0.84	55	8.7 (8.5±0.15)

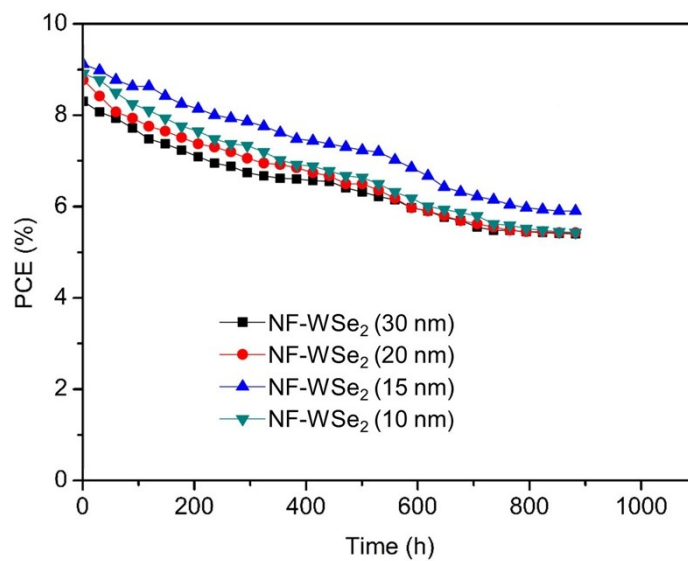


Fig. s12. Power conversion efficiency (PCE) of PBDB-T:PC₇₁BM+bCar-based PSCs with thickness-dependent NF-WSe₂ for HTL as a function of aging time.

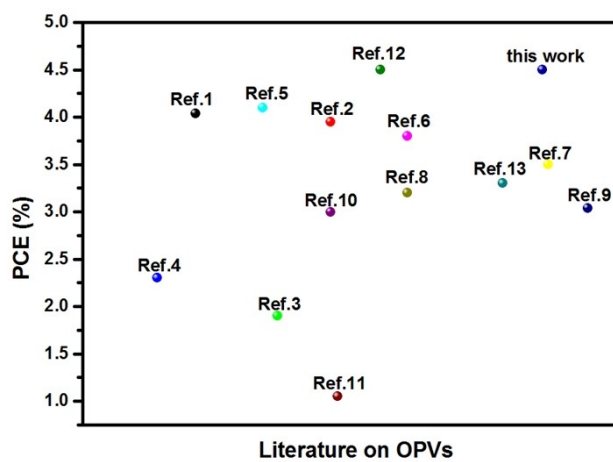


Fig. s13. A comparison of the performance with previously reported OPVs based on PCDTBT:PCBM BHJ.

Table s3. Comparison of the performance specifications of PCDTBT:PCBM BHJ solar cells in Fig. s9.

Active layer	HTL	Thickness of HTL (nm)	PCE (%)	V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF (%)	Resistance value (Ω)	Fatigue endurance	Ref.
PCDTBT:PC ₆₀ BM	PEDOT:PSS	30–40	4.04	0.904	7.7	58	Not shown	none	[1]
PCDTBT:PC ₆₁ BM	MoO ₃		3.95	0.92	7.4	58	Not shown	none	[2]
PCDTBT:PC ₇₁ BM	MoO ₃	20	1.9	0.57	8.69	38	Not shown	none	[3]
PCDTBT:PC ₆₁ BM			2.3	0.87	5.3	49	series resistance (R_s) is 50	none	[4]
PCDTBT:PC ₆₁ BM	MoO ₃	3	4.1	0.871	7.8	60	Not shown	none	[5]
PCDTBT:PCBM-Ag NPs			3.8	0.853	7.3	67	Not shown	none	[6]
PCDTBT:PC ₇₀ BM	PEDOT:PSS with Pentacene	50	3.5	0.82	9.7	44	series resistance (R_s) is 19	none	[7]
P2:PC ₆₀ BM	PEDOT:PSS		3.2	0.78	9.31	44	Not shown	none	[8]
PCDTBT:PC ₆₁ BM (PCB)2C2 (30%)	PEDOT:PSS		3.04	0.95	6.4	50	Not shown	none	[9]
PCDTBT:PC ₆₁ BM	PEDOT:PSS	20	3.0	0.75	8.53	43	Not shown	none	[10]
PCDTBT:PC ₆₁ BM + PQT-12	PEDOT:PSS	40	1.05	0.562	5.62	33	Not shown	none	[11]
PCDTBT:PC ₆₀ BM	MoO ₃	10	4.5				Not shown	PCE loss of 40% after 330 h	[12]
PCDTBT:PC ₆₁ BM	PEDOT:PSS	30	3.3	0.7	12.5	38	Not shown	Less than 40% of initial PCE after 1000h	[13]
PCDTBT:PC ₇₁ BM +bCar	WSe ₂	15	4.5	0.89	9.7	53.7	series resistance (R_s) is 19; device resistance (R_d) is 244	Above 80% of initial PCE after 1000h	This work

Supporting references

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